

MOSFETs Silicon N-Channel MOS (DTMOSIV)

# **TK8P60W5**

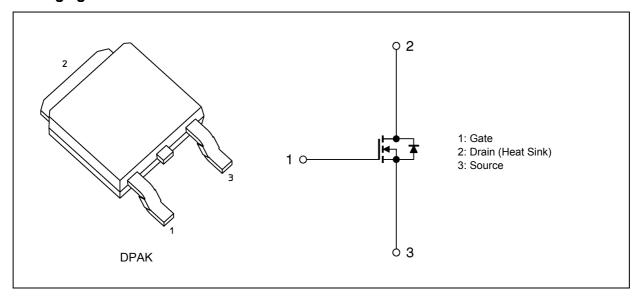
## 1. Applications

- Switching Voltage Regulators
- · Motor Drivers

#### 2. Features

- (1) Fast reverse recovery time:  $t_{rr} = 80 \text{ ns (typ.)}$
- (2) Low drain-source on-resistance:  $R_{DS(ON)}$  = 0.44  $\Omega$  (typ.) by used to Super Junction Structure: DTMOS
- (3) Easy to control Gate switching
- (4) Enhancement mode:  $V_{th}$  = 3 to 4.5 V ( $V_{DS}$  = 10 V,  $I_{D}$  = 0.4 mA)

#### 3. Packaging and Internal Circuit





## 4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	600	V
Gate-source voltage		$V_{GSS}$	±30	
Drain current (DC)	(Note 1)	I <sub>D</sub>	8.0	Α
Drain current (pulsed)	(Note 1)	I <sub>DP</sub>	32	
Power dissipation $(T_c = 25^\circ)$	°C)	$P_{D}$	80	W
Single-pulse avalanche energy	(Note 2)	E <sub>AS</sub>	105	mJ
Avalanche current		I <sub>AR</sub>	2.0	Α
Reverse drain current (DC)	(Note 1)	I <sub>DR</sub>	8.0	
Reverse drain current (pulsed)	(Note 1)	I <sub>DRP</sub>	32	
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature		T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R <sub>th(ch-c)</sub>	1.57	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 46.0 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 2.0 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



#### 6. Electrical Characteristics

## 6.1. Static Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	_		±1	μА
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V	_	_	100	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	600	_	_	V
Gate threshold voltage	$V_{th}$	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.4 mA	3	_	4.5	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.0 A		0.44	0.56	Ω

## 6.2. Dynamic Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 300 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	590		pF
Reverse transfer capacitance	$C_{rss}$		_	1.7		
Output capacitance	C <sub>oss</sub>		_	16		
Effective output capacitance	C <sub>o(er)</sub>	V <sub>DS</sub> = 0 to 400 V, V <sub>GS</sub> = 0 V	_	33	_	
Gate resistance	r <sub>g</sub>	V <sub>DS</sub> = OPEN, f = 1 MHz	_	7.5	_	Ω
Switching time (rise time)	t <sub>r</sub>	See Figure 6.2.1	_	40		ns
Switching time (turn-on time)	t <sub>on</sub>		_	60	_	
Switching time (fall time)	t <sub>f</sub>		_	5.5		
Switching time (turn-off time)	t <sub>off</sub>		_	70	_	
MOSFET dv/dt ruggedness	dv/dt	V <sub>DD</sub> = 0 to 400 V, I <sub>D</sub> = 4.0 A	50	_	_	V/ns

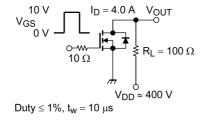


Fig. 6.2.1 Switching Time Test Circuit

#### 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 8.0 \text{ A}$	_	22		nC
Gate-source charge 1	Q <sub>gs1</sub>		_	7.5		
Gate-drain charge	$Q_{gd}$		_	13	_	

## 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	$V_{DSF}$	I <sub>DR</sub> = 8.0 A, V <sub>GS</sub> = 0 V	-	1	-1.7	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 4.0 A, V <sub>GS</sub> = 0 V -dI <sub>DR</sub> /dt = 100 A/μs		80	128	ns
Reverse recovery charge	$Q_{rr}$			0.35		μС
Peak reverse recovery current	I <sub>rr</sub>		_	9.2	_	Α
Diode dv/dt ruggedness	dv/dt	I <sub>DR</sub> = 4.0 A, V <sub>GS</sub> = 0 V, V <sub>DD</sub> = 400 V	50		_	V/ns



## 7. Marking

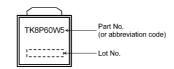


Fig. 7.1 Marking

#### 8. Characteristics Curves (Note)

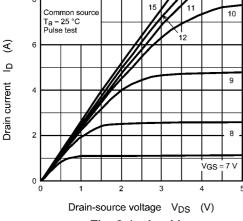
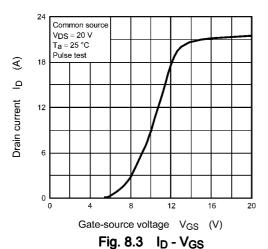


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>



Common source VGS = 0 V ID = 10 mA Pulse test

 $\Im$ 

SSQV 650

 $\label{eq:model} \begin{array}{ll} \mbox{Ambient temperature} & \mbox{$T_a$} & (^{\circ}\mbox{$C$}) \\ \mbox{Fig. 8.5} & \mbox{$V_{DSS}$} - \mbox{$T_a$} \end{array}$ 

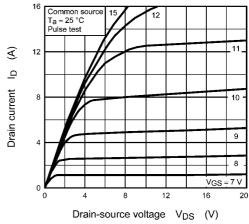
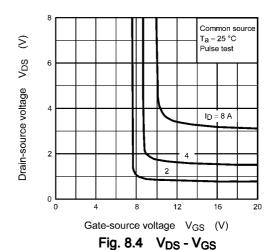


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>



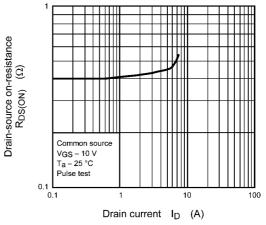


Fig. 8.6 R<sub>DS(ON)</sub> - I<sub>D</sub>

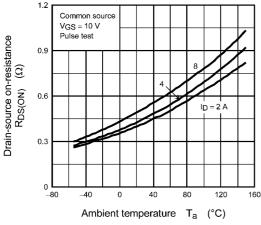


Fig. 8.7 R<sub>DS(ON)</sub> - T<sub>a</sub>

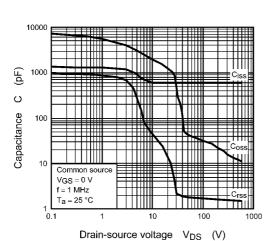


Fig. 8.9 C - V<sub>DS</sub>

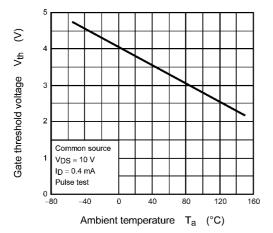


Fig. 8.11 V<sub>th</sub> - T<sub>a</sub>

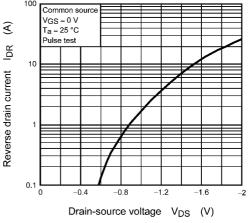


Fig. 8.8 IDR - VDS

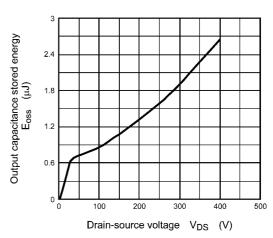


Fig. 8.10 E<sub>OSS</sub> - V<sub>DS</sub>

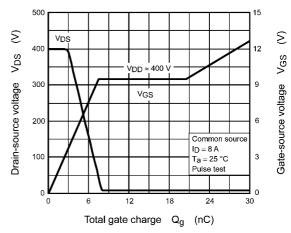


Fig. 8.12 Dynamic Input/Output Characteristics

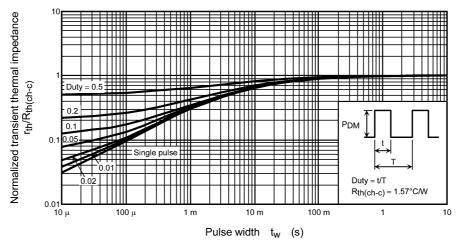


Fig. 8.13 r<sub>th</sub> - t<sub>w</sub> (Guaranteed Maximum)

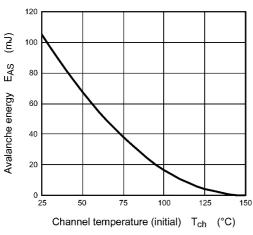


Fig. 8.14 E<sub>AS</sub> - T<sub>ch</sub> (Guaranteed Maximum)

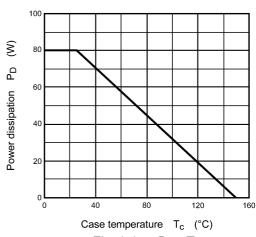


Fig. 8.15  $P_D - T_c$  (Guaranteed Maximum)

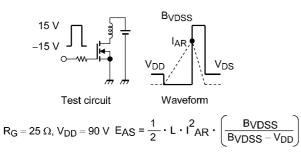


Fig. 8.16 Test Circuit/Waveform

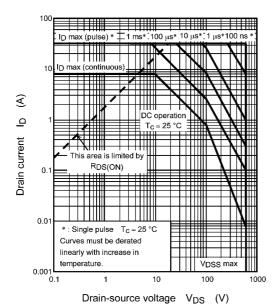


Fig. 8.17 Safe Operating Area (Guaranteed Maximum)

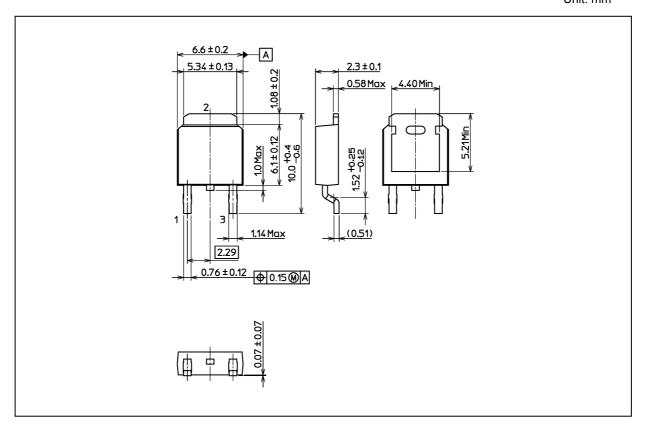
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

**TK8P60W5** 



## **Package Dimensions**

Unit: mm



Weight: 0.36 g (typ.)

Package Name(s)
TOSHIBA: 2-7K1S
Nickname: DPAK

Rev.6.0



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